

# PMEG3002AEL

30 V, 0.2 A very low V<sub>F</sub> MEGA Schottky barrier rectifier in leadless ultra small SOD882 package

Rev. 02 — 15 January 2010

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection encapsulated in a SOD882 leadless ultra small plastic package.

### 1.2 Features

- Forward current: 0.2 A
- Reverse voltage: 30 V
- Very low forward voltage
- Leadless ultra small plastic package
- Power dissipation comparable to SOT23

### 1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Low voltage rectification
- High efficiency DC-to-DC conversion
- Low power consumption applications

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current		-	-	0.2	Α
$V_R$	reverse voltage		-	-	30	V



## 2. Pinning information

Table 2. Discrete pinning

	<u> </u>	
Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 2 sym001  Bottom view  Top view  001aaa332

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG3002AEL	-	leadless ultra small plastic package; 2 terminals; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOD882			

# 4. Marking

Table 4. Marking

Type number	Marking code
PMEG3002AEL	F3

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{R}$	continuous reverse voltage			-	30	V
I <sub>F</sub>	continuous forward current			-	0.2	Α
$I_{FRM}$	repetitive peak forward current	$t_p \leq \text{1 ms; } \delta \leq 0.25$		-	1	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms square wave		-	3	Α
Tj	junction temperature		[1]	-	150	°C
T <sub>amb</sub>	operating ambient temperature		[1]	-65	+150	°C
T <sub>stg</sub>	storage temperature			-65	+150	°C

[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses. Nomograms for determining the reverse power losses P<sub>R</sub> and I<sub>F(AV)</sub> rating will be available on request.

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	500	K/W

<sup>[1]</sup> Refer to SOD882 standard mounting conditions (footprint), FR4 with 60  $\mu$ m copper strip line.

### 7. Characteristics

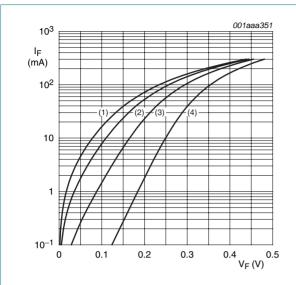
Table 7. Characteristics

 $T_{amb} = 25 \, ^{\circ}\text{C}$  unless otherwise specified.

	<del>-</del>					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub> continuous forward voltage	continuous forward	see Figure 1;				
	voltage	I <sub>F</sub> = 0.1 mA	-	125	190	mV
		I <sub>F</sub> = 1 mA	-	185	250	mV
		I <sub>F</sub> = 10 mA	-	250	300	mV
		I <sub>F</sub> = 100 mA	-	350	400	mV
	$I_F = 200 \text{ mA}$	-	420	480	mV	
I <sub>R</sub>	continuous reverse	see Figure 2; [1]				
	current	V <sub>R</sub> = 10 V	-	2.5	10	μΑ
		V <sub>R</sub> = 30 V	-	10	50	μΑ
$C_d$	diode capacitance	$V_R = 1 V; f = 1 MHz;$ see <u>Figure 3</u>	-	17	25	pF

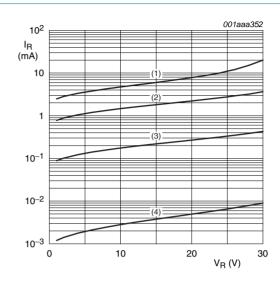
<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02.$ 

<sup>[2]</sup> For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses. Nomograms for determining the reverse power losses  $P_R$  and  $I_{F(AV)}$  rating will be available on request.



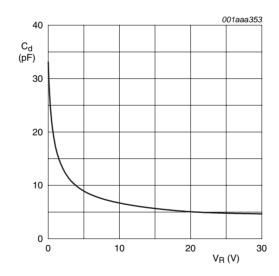
- (1)  $T_j = 150 \, ^{\circ}C$
- (2)  $T_i = 125 \, ^{\circ}\text{C}$
- (3)  $T_i = 85 \, ^{\circ}C$
- (4)  $T_i = 25 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_j = 150 \, ^{\circ}C$
- (2)  $T_i = 125 \,^{\circ}\text{C}$
- (3)  $T_i = 85 \, ^{\circ}C$
- (4)  $T_j = 25 \, ^{\circ}\text{C}$

Fig 2. Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$ 

Fig 3. Diode capacitance as a function of reverse voltage; typical values

**EUROPEAN** 

**PROJECTION** 

**ISSUE DATE** 

03-04-16

03-04-17

## 8. Package outline

Leadless ultra small plastic package; 2 terminals; body 1.0 x 0.6 x 0.5 mm

**SOD882** 

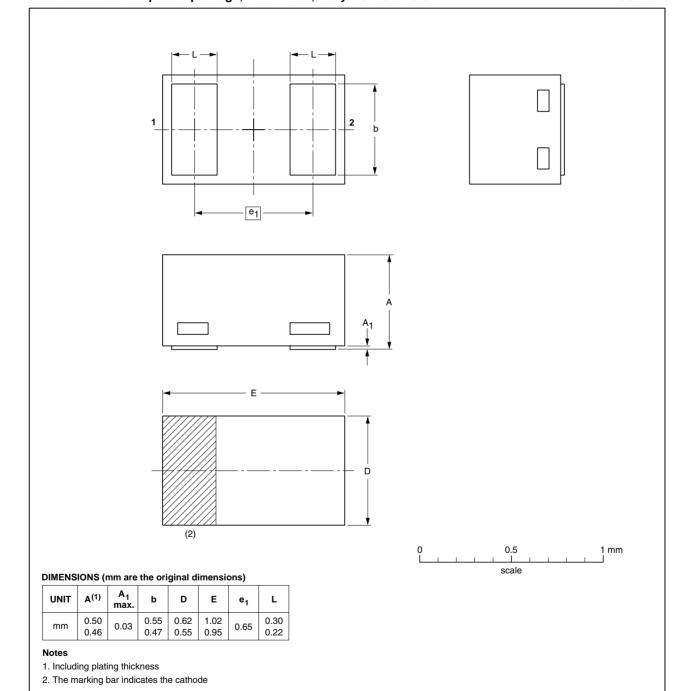


Fig 4. Package outline

OUTLINE

VERSION

SOD882

JEITA

REFERENCES

**JEDEC** 

IEC



# 9. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3002AEL_2	20100115	Product data sheet	-	PMEG3002AEL_1
Modifications:		eet was changed to reflect w legal definitions and disc		
PMEG3002AEL_1	20040224	Product data	-	-

## 10. Legal information

### 10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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# PMEG3002AEL

## 0.2 A very low V<sub>F</sub> MEGA Schottky barrier rectifier

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